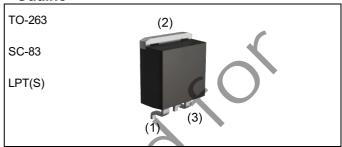
Nch 600V 15A Power MOSFET

V _{DSS}	600V
R _{DS(on)} (Max.)	0.35Ω
I _D	±15A
P _D	255W

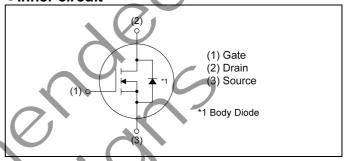
●Outline



Features

- 1) Fast reverse recovery time (trr).
- 2) Low on-resistance.
- 3) Fast switching speed.
- 4) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 5) Drive circuits can be simple.
- 6) Pb-free lead plating; RoHS compliant

Inner circuit



Packaging specifications

- 1 001101	Jg 5 5 5 5 5 5 5 5 5 5	
(Packing	Embossed Tape
(7)	Reel size (mm)	330
Туре	Tape width (mm)	24
	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	R6015FNJ

Application

Switching Power Supply

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	7	V_{DSS}	600	V
Continuous dusin suument	T _C = 25°C	I _D *1	±15	Α
Continuous drain current	T _C = 100°C	I _D *1	±7.3	А
Pulsed drain current	l _{DP} *2	±60	Α	
Gate - Source voltage		V_{GSS}	±30	V
Avalanche current, single pulse		I _{AS} *3	7.5	Α
Avalanche energy, single pulse	E _{AS} *3	15	mJ	
Avalanche energy, repetitive		E _{AR} *4	3.5	mJ
Power dissipation (T _c = 25°C)		P_{D}	255	W
Junction temperature		T _j	150	°C
Operating junction and storage temperature range		T _{stg}	-55 to +150	°C
Reverse diode dv/dt		dv/dt	15	V/ns

● Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_{D} = 15A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Min	Values Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-(-	0.49	°C/W
Thermal resistance, junction - ambient	R _{thJA}	7	-	80	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}		-	265	°C

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	9	Values		Unit
r al al nie lei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = 1mA$	600	-	-	V
Drain - Source avalanche breakdown voltage	V _{(BR)DS}	$V_{GS} = 0V, I_D = 7.5A$	ı	700	-	V
\sim		$V_{DS} = 600V, V_{GS} = 0V$				
Zero gate voltage drain current	J _{DSS}	$T_j = 25^{\circ}C$	-	1	100	μΑ
X	7	$T_j = 125^{\circ}C$	-	-	10000	
Gate - Source leakage current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 1mA	3	-	5	V
		V _{GS} = 10V, I _D = 7.5A				_
Static drain - source on - state resistance	R _{DS(on)} *6	$T_j = 25^{\circ}C$	-	0.27	0.35	Ω
on state regionality		$T_j = 125^{\circ}C$	-	0.59	-	
Gate resistance	R_{G}	f = 1MHz, open drain	-	10.2	-	Ω

● Electrical characteristics (T_a = 25°C)

Parameter Symbol Conditions			Values		Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Forward Transfer Admittance	Y _{fs} *6	V _{DS} = 10V, I _D = 7.5A	4.5	10	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	1	1660		•
Output capacitance	C _{oss}	V _{DS} = 25V	-	1110		pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	45	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V,		54.6	-	E
Effective output capacitance, time related	C _{o(tr)}	V _{DS} = 0V to 480V		183	-	pF
Turn - on delay time	t _{d(on)} *6	V _{DD} ≈ 300V, V _{GS} = 10V	- (38)	-	
Rise time	t _r *6	I _D = 7.5A	+	45	-	
Turn - off delay time	t _{d(off)} *6	$R_L \simeq 40.2\Omega$	1	120	240	ns
Fall time	t _f *6	$R_G = 10\Omega$	J	35	70	

● Gate charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions		Values		Unit
	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{\star 6}$	V _{DD} ≈ 300V	-	42	-	
Gate - Source charge	Q _{gs} *6	I _D = 15A	-	12	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	•	20	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 300V$, $I_D = 15A$	-	7.6	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw ≤ 10μs, Duty cycle ≤ 1%

^{*3} L \simeq 500 μ H, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25°C

^{*4} L \simeq 500 μ H, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25 $^{\circ}$ C, f=10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Downwater	Curanh al	Conditions	Values			1.1-24
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	I _S *1	T - 25°0	-	-	15	А
Pulse forward current	I _{SP} *2	T _C = 25°C	-	- 6	60	A
Forward voltage	V _{SD} *6	V _{GS} = 0V, I _S = 15A	-	- ~	1.5	V
Reverse recovery time	t _{rr} *6		-	90	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 15A di/dt = 100A/µs		0.44	-	μC
Peak reverse recovery current	I _{rrm} *6	- αι/αι – 100/4μ3	V	7.0	-	Α
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C):	1000	-	A/µs

Typical transient thermal characteristics

Symbol	Value	Unit
R _{th1}	0.0559	
R _{th2}	0.210	K /W
R _{th3}	0.603	

Symbol	Value	Unit
C _{th1}	0.00256	
C _{th2}	0.095	Ws/K
C_{th3}	0.212	

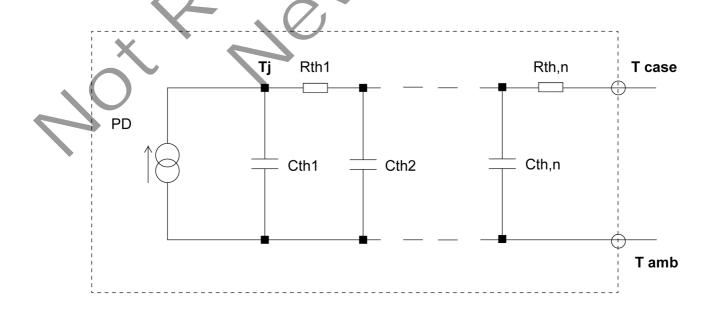


Fig.1 Power Dissipation Derating Curve

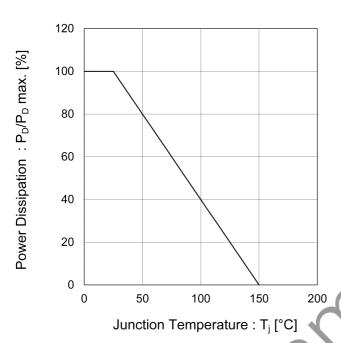


Fig.2 Maximum Safe Operating Area

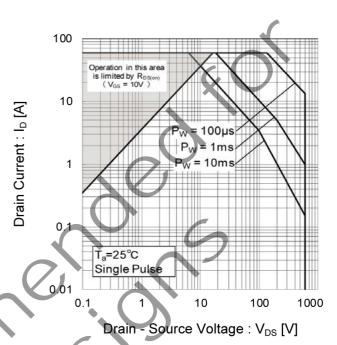
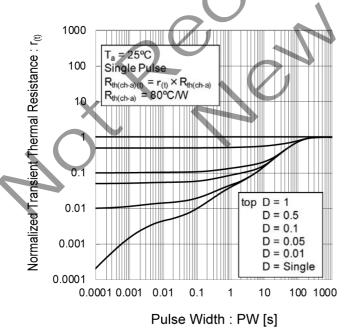


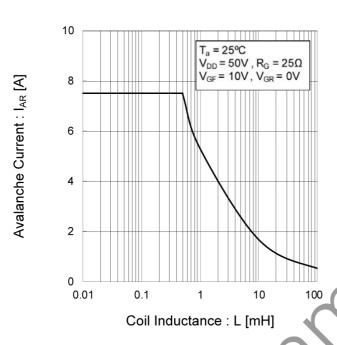
Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



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Fig.4 Avalanche Current vs. Inductive Load

Fig.5 Avalanche Power Losses



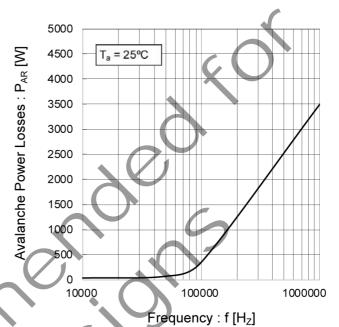


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature

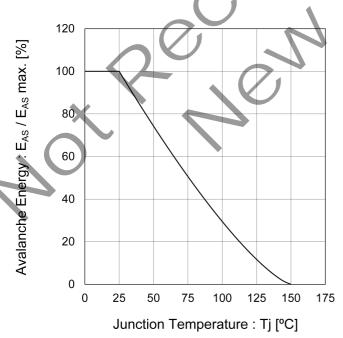
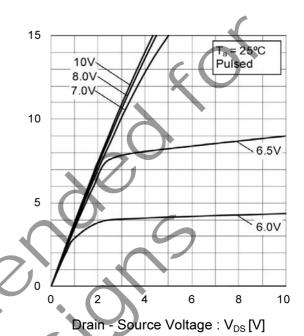


Fig.7 Typical Output Characteristics(I)

15 $T_a = 25$ °C 8.0V 7.0V Drain Current : I_D [A] 10 5 6.0V 0 0 10 20 30 40 50 Drain - Source Voltage : $V_{DS}[V]$

Fig.8 Typical Output Characteristics(II)



Drain Current : I_D [A]

Fig.9 Tj = 150°C Typical Output Characteristics (I)

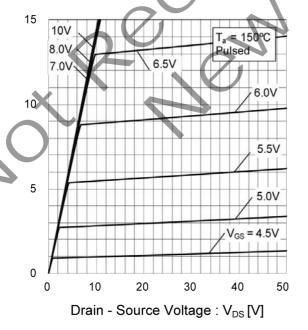
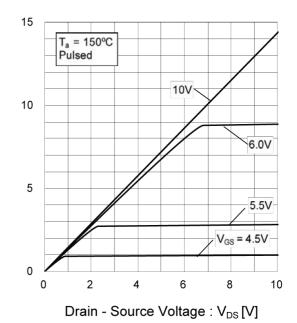


Fig.10 Tj = 150°C Typical Output Characteristics (II)



Drain Current : I_D [A]

Fig.11 Breakdown Voltage vs. Junction Temperature

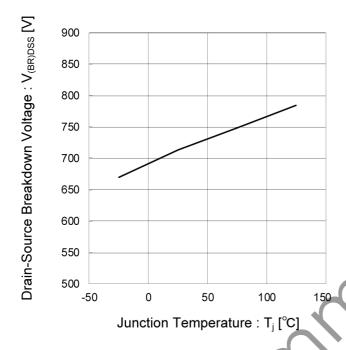


Fig.12 Typical Transfer Characteristics

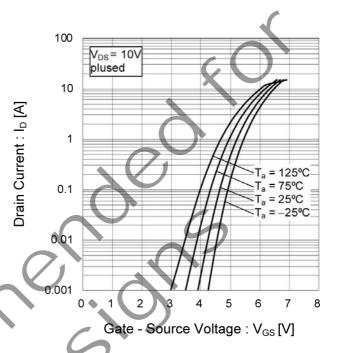


Fig.13 Gate Threshold Voltage vs. Junction Temperature

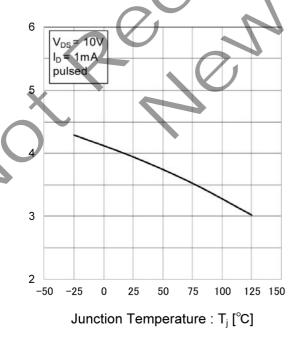
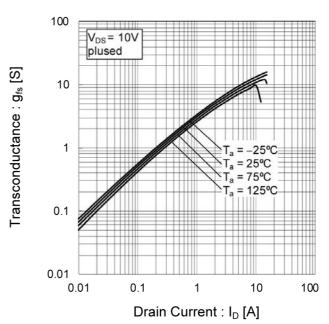


Fig.14 Transconductance vs. Drain Current



Gate Threshold Voltage: V_{GS(th)} [V]

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

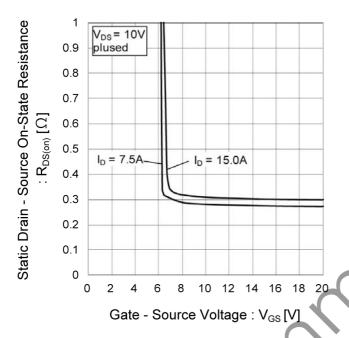


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

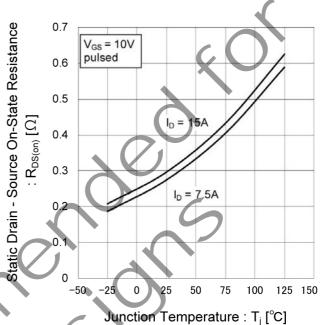


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

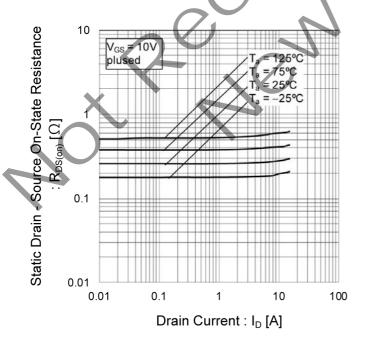


Fig.18 Typical Capacitance vs. Drain - Source Voltage

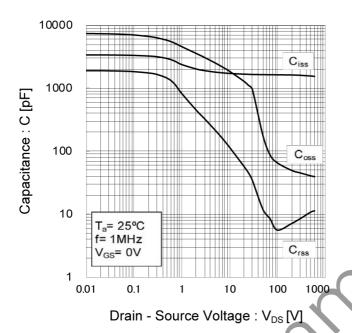
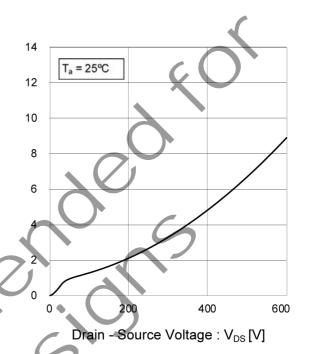


Fig.19 Coss Stored Energy



Coss Stored Energy : E $_{
m oss}$ [μ J]

Fig.20 Switching Characteristics

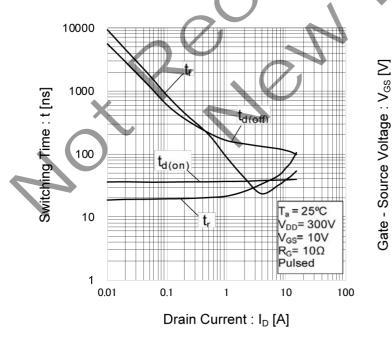
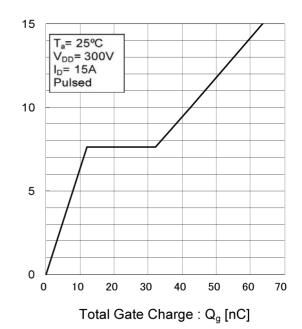


Fig.21 Dynamic Input Characteristics



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Inverse Diode Forward Current : Is [A]

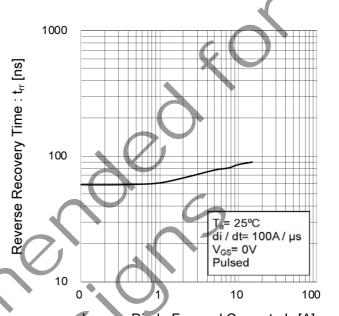
Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

100
V_{GS} = 0V
plused

10
T_a = 125°C
T_a = 75°C
T_a = 25°C
T_a = -25°C

0.1
0.01
0.00
0.5
1.0
1.5
Source - Drain Voltage: V_{SD} [M]

Fig.23 Reverse Recovery Time vs.
Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

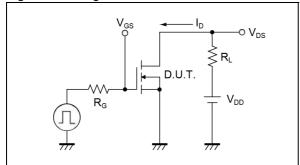


Fig.2-1 Gate Charge Measurement Circuit

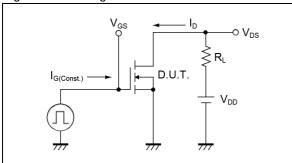


Fig.3-1 Avalanche Measurement Circuit

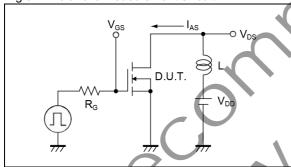


Fig.4-1 dv/dt Measurement Circuit

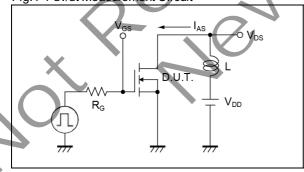


Fig.5-1 di/dt Measurement Circuit

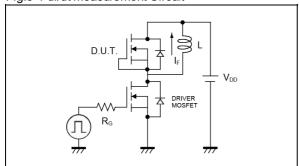


Fig.1-2 Switching Waveforms

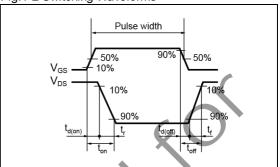


Fig.2-2 Gate Charge Waveform

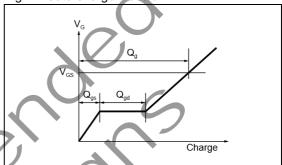


Fig.3-2 Avalanche Waveform

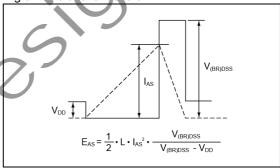


Fig.4-2 dv/dt Waveform

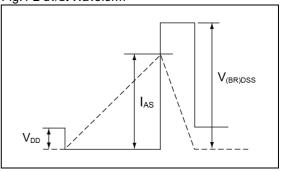
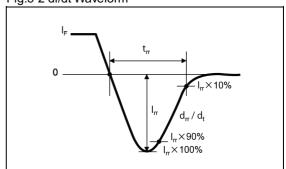
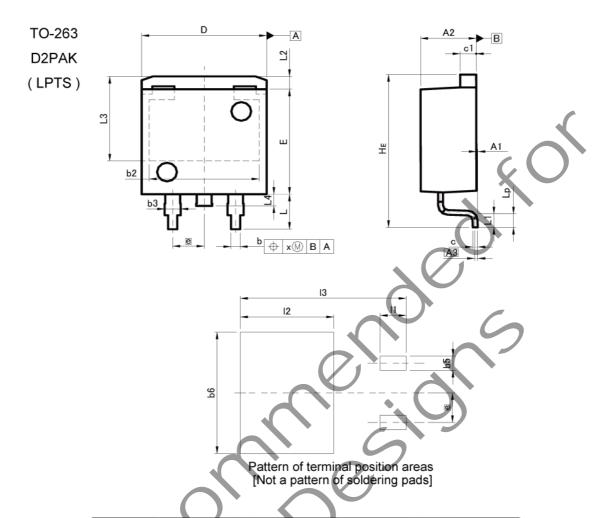


Fig.5-2 di/dt Waveform



Dimensions



DIM	MILIM	MILIMETERS		HES
DIM	■ MIN	MAX	MIN	MAX
A1	0.00	0.30	0.000	0.012
A2	4.30	4.70	0.169	0.185
A3	0	.25	0.0	10
b	0.68	0.98	0.027	0.039
62	8	.90	0.3	350
b3	1.14	1.44	0.045	0.057
С	0.30	0.60	0.012	0.024
c1	1.10	1.50	0.043	0.059
D	9.80	10.40	0.386	0.409
E	8.80	9.20	0.346	0.362
е	2	.54	0.100	
HE	12.80	13.40	0.504	0.528
L	2.70	3.30	0.106	0.130
L1	1	.20	0.0	147
L2	1	1.10		143
L3	7	7.25		285
L4	1	.00	0.0	39
Lp	0.90	1.50	0.035	0.059
X	= 2	0.25	=	0.010

DIM	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
b5	=:	1.23	-	0.049
b6	= 0	10.40		0.409
11	<u>22</u> 8	2.10	, 12	0.083
12	 .	7.55	1.00	0.297
13	_	13 40	-	0.528

Dimension in mm/inches

Notice

Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASS II b	CLASSIII
CLASSIV	CLASSIII	CLASSⅢ	CLASSIII

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 - [a] Installation of protection circuits or other protective devices to improve system safety
 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are designed and manufactured for use under standard conditions and not under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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